

TriQuint wins Navy contract for high voltage GaAs

The US Office of Naval Research (ONR) has awarded TriQuint a 20-month, \$3.1m contract to improve manufacturing methods of producing high-power, high-voltage S-band GaAs amplifiers.

According to TriQuint's Contract Program Manager and Director of R&D, Anthony Balistreri, the company's high voltage pHEMT technology provides the higher power density and efficiency required for near-term production applications for the Navy, including phased array radar, electronic warfare and communications systems. TriQuint has been developing the high voltage pHEMT technology since 2000, an advanced X-band version of that process was developed under a previous ONR contract.

The new program has two primary objectives, split into phases, or 'tasks': an MMIC design optimization task followed by a manufacturing cost reduction task. Under the first phase, TriQuint will design an S-band high power amplifier suitable for a wide range of applications. This initial design will be updated throughout the program and will be used to validate manufacturing process improvements. Overall design goals include high power and efficiency with a minimum 24V operating voltage. The contract's primary focus is manufacturing, with two principal goals: reducing cost and improving throughput. Contract 'sub-tasks' are designed to improve manufacturing variability,

reduce cycle time and improve wafer and device yields. TriQuint is the sole contractor and is performing the work at its Richardson, Texas facility.

remarking about the new contract, Dr. Gailon Brehm, TriQuint's military business unit director said, "TriQuint currently supplies high volume, cost effective foundry services and standard products based on high voltage GaAs. This enhanced S-band technology provides the higher voltage needed for both military and commercial applications at frequencies below 6 GHz."

TriQuint also announced a new design and support center in High Point, North Carolina.

For more details, visit: www.triquint.com

Nitronex funding boost for GaN RF

The Raleigh, NC, USA, manufacturer of GaN RF power transistors, Nitronex, recently closed a \$21.8m round of venture funding led by Alloy Ventures and other new investors.

Earlier Nitronex had raised \$9.5m in November 2000, \$11.3m in July 2003 and \$6m in April 2004. It recently launched a family of RF power transistors for WiMax based on its Sigantic process

representing the first GaN-based power transistor products grown on silicon for the commercial and broadband wireless markets, it said.

Now it plans to use the latest capital to complete the development and expand manufacturing of products; accelerate hiring in operations, engineering, sales and marketing and finance; and expand into global markets.

"We believe that our GaN-on-silicon based products offer significant advantages over existing LDMOS and GaAs solutions for the WiMax, cellular, and broadband wireless markets. With our new financing, we plan to accelerate our efforts to introduce a broad family of innovative RF power transistor products for these markets," said Charles Shalvoy, Nitronex CEO.

For more details, visit: www.nitronex.com